

Description

The DFI600HF17I4RE2 is a Half Bridge IGBT Power Module. It integrates high performance IGBT chips designed for the applications such as High Power supply and Motor control.



Features

- Blocking voltage:1700V
- Low saturation voltage $V_{CE(sat)}$
- Low Switching Losses
- 175°C maximum junction temperature
- Thermistor inside

Applications

- High Power Switching Applications
- Motor Drives
- Solar inverter Systems
- Wind Turbines

Circuit diagram

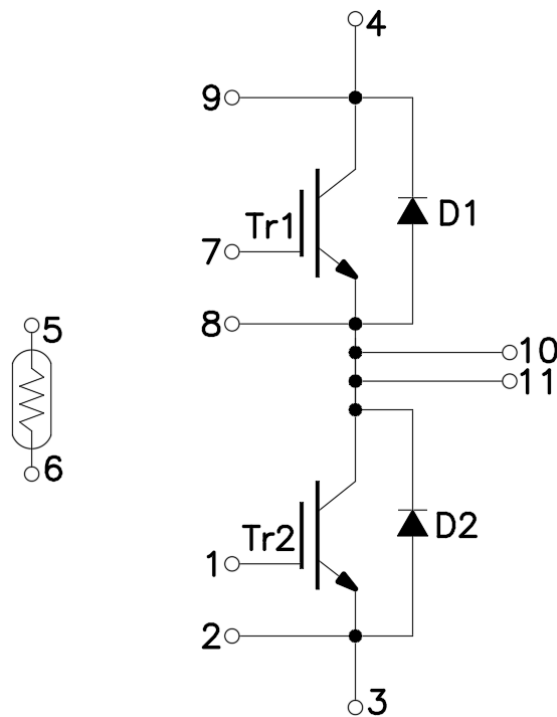


Figure 1. Out drawing & circuit diagram for DFI600HF17I4RE2

Pin Configuration and Marking Information

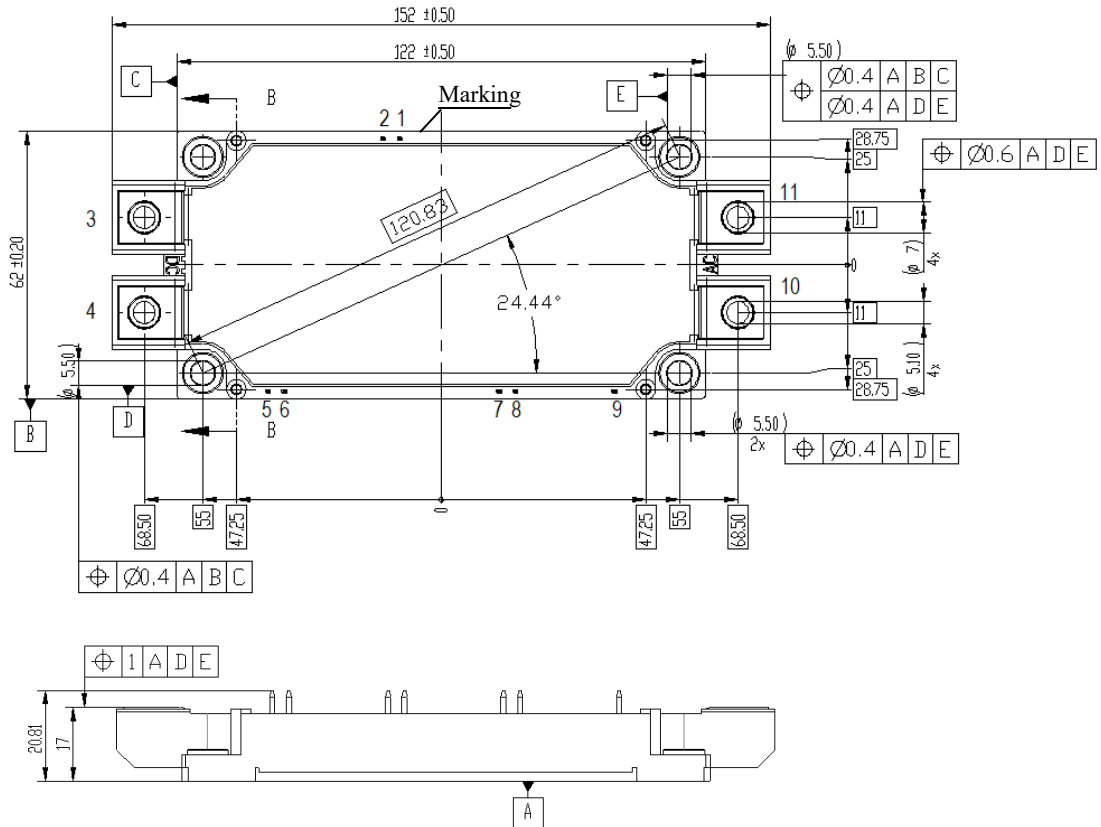


Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f = 50Hz, t = 1 min	4.0	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 13	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	>225	-
Module lead resistance, terminals–chip	T _c = 25°C	0.8	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	420	g

Maximum Ratings (T_j=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-Emitter Voltage	G-E Short	1700	V
V _{GES}	Gate-Emitter Voltage	C-E Short	±30	V
I _C	DC Continuous Collector Current	T _C =100°C	650	A
I _{CM}	Pulse Collector Current	t _p =1ms, Note1	1300	A
P _C	Maximum Power Dissipation	T _C =25°C, T _j =175°C(IGBT)	4687	W
I _F	Diode Forward Current	-	600	A
I _{FRM}	Repetitive peak forward Current	t _p =1ms, Note1	1200	A
I ² t	I ² t-value	V _R =0V, t _p =10ms, T _j =125°C (Diode)	20000	A ² s
T _{jmax}	Max junction temperature	-	175	°C
T _{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-value	R ₂ = R ₂₅ exp [B _{25/50} (1/T ₂ - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R ₂ = R ₂₅ exp [B _{25/80} (1/T ₂ - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R ₂ = R ₂₅ exp [B _{25/100} (1/T ₂ - 1/(298,15 K))]	-	3433	-	K

IGBT Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{CE(sat)} (Chip)	Collector-Emitter Saturation Voltage	I _C =600A V _{GE} =15V	T _j =25°C	-	1.60	1.92	V
			T _j =150°C	-	1.88	-	V
			T _j =175°C	-	1.93	-	V
V _{GE(th)}	Gate-Emitter threshold Voltage	I _C =24mA, V _{CE} =V _{GE}		5.2	5.8	6.4	V
I _{CES}	Collector- Emitter Cut off Current	V _{CE} =1700V, V _{GE} =0V	T _j =25°C	-	-	1	mA
I _{GES}	Gate-Emitter Leakage Current	V _{GE} =20V, V _{CE} =0V	T _j =25°C	-	-	1.8	uA
C _{ies}	Input Capacitance	V _{CE} =25V V _{GE} =0V f=1MHz	T _j =25°C	-	49.5	-	nF
C _{oes}	Output Capacitance		T _j =25°C	-	1.8	-	nF
C _{res}	Reverse transfer Capacitance		T _j =25°C	-	0.75	-	nF
Q _G	Gate charge	V _{GE} = -15V to +15V		-	6.2	-	uC
R _{Gint}	Internal gate resistor	-	T _j =25°C	-	1.7	-	Ω
t _{d(on)}	Turn-on delay time	V _{CC} =900V I _C = 600A V _{GE} =+15V/-8V R _G =1.0Ω Inductive load	T _j =25°C	-	205	-	ns
			T _j =150°C	-	207	-	
t _r	Rise time		T _j =25°C	-	125	-	ns
			T _j =150°C	-	188	-	
t _{d(off)}	Turn-off delay time		T _j =25°C	-	570	-	ns
			T _j =150°C	-	735	-	
t _f	Fall time		T _j =25°C	-	370	-	ns
			T _j =150°C	-	680	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	234	-	mJ
			T _j =150°C	-	383	-	
E _{off}	Turn-off power dissipation		T _j =25°C	-	134	-	mJ
			T _j =150°C	-	205	-	
I _{SC}	SC data	V _{GE} <15V V _{CC} =1000V	T _j =150°C t _p <10us	-	3000	-	A
R _{th(j-c)}	Thermal Resistance, Junction to Case (IGBT)			-	0.032	-	°C /W
R _{th(c-s)}	Thermal Resistance, Case to sink (Conductive Grease applied)			-	0.015	-	°C /W

Freewheeling Diode Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition	Value			Unit	
			Min.	Typ.	Max		
V _F	Diode Forward Voltage	I _F =600A, V _{GE} =0V	T _j =25°C	-	2.10	-	V
			T _j =150°C	-	2.32	-	
			T _j =175°C	-	2.29	-	
t _{rr}	Reverse recovery time	(Switch side) V _{CC} =900V, I _C =600A V _{GE} =+15V/-8V	T _j =25°C	-	1.03	-	us
			T _j =150°C	-	1.39	-	
I _{RM}	Peak reverse recovery Current	R _G =1.0Ω (FRD side)	T _j =25°C	-	210	-	A
			T _j =150°C	-	277	-	
Q _{rr}	Recovered charge	V _{rr} =900V, I _F =600A V _{GE} =+15V/-8V	T _j =25°C	-	83	-	uC
			T _j =150°C	-	192	-	
E _{rr}	Reverse recovered energy	Inductive load switching operation	T _j =25°C	-	49.7	-	mJ
			T _j =150°C	-	127	-	
R _{th(j-c)}	Thermal Resistance, Junction to Case (Diode)		-	0.060	-	°C/W	
R _{th(c-s)}	Thermal Resistance, Case to sink (Conductive Grease applied)		-	0.015	-	°C/W	

Test Conditions

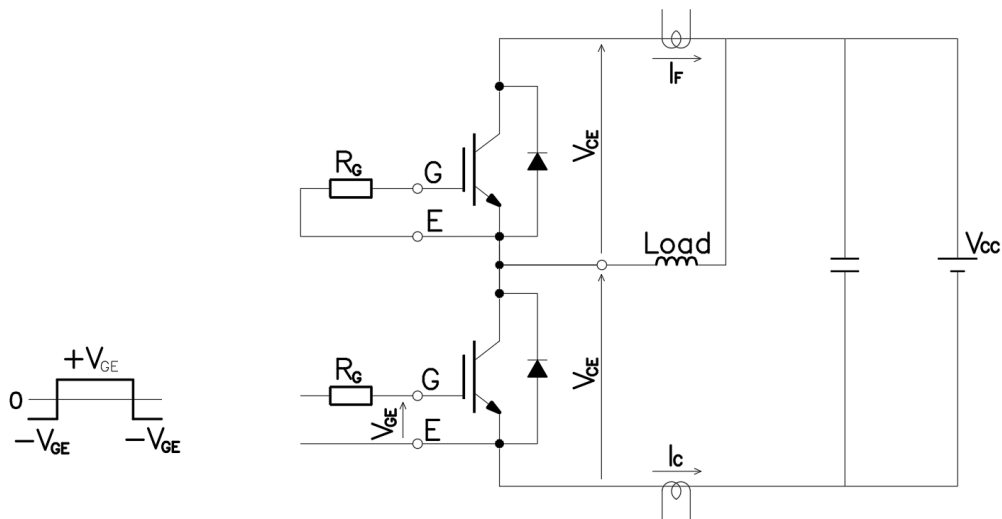


Figure 3. Switching time measure circuit

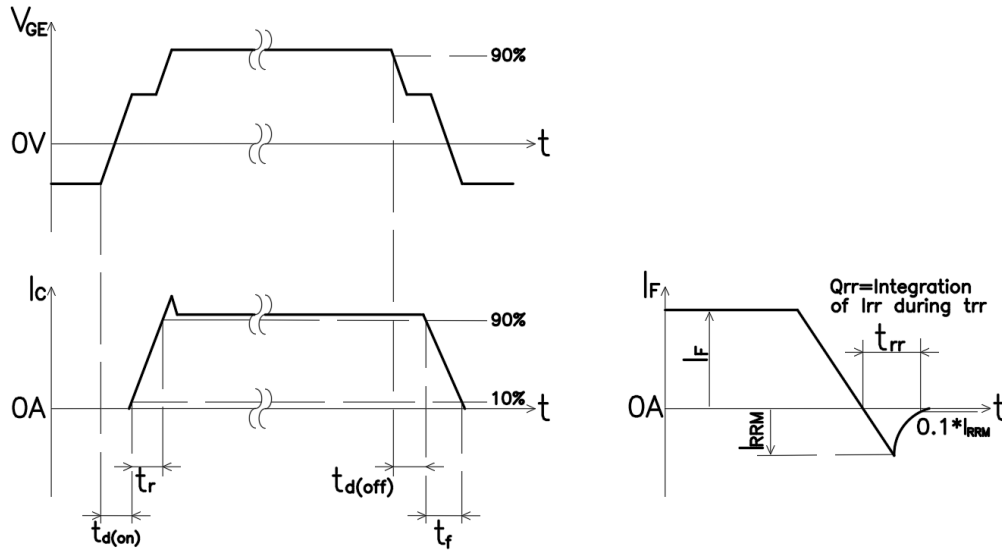


Figure 4. Switching time definition

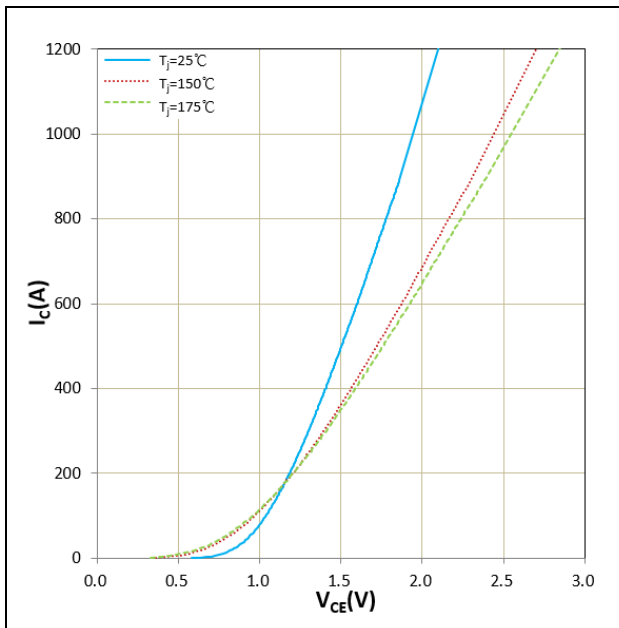


Figure 5. I_c vs V_{CE}
 $V_{GE} = 15V$

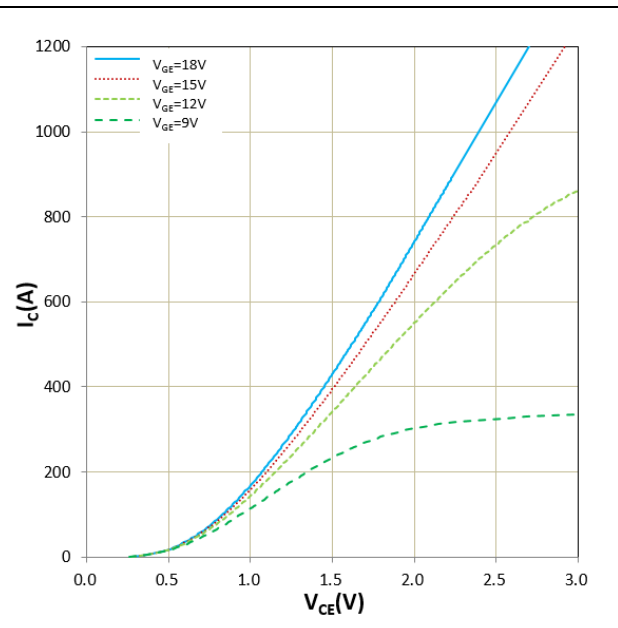


Figure 6. I_c vs V_{CE}
 $T_j = 175^\circ C$

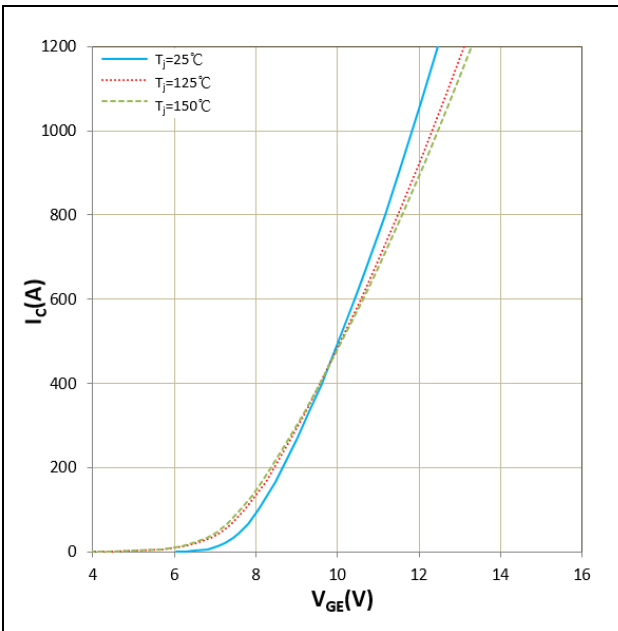


Figure 7. I_c vs V_{GE}
 $V_{CE} = 20V$

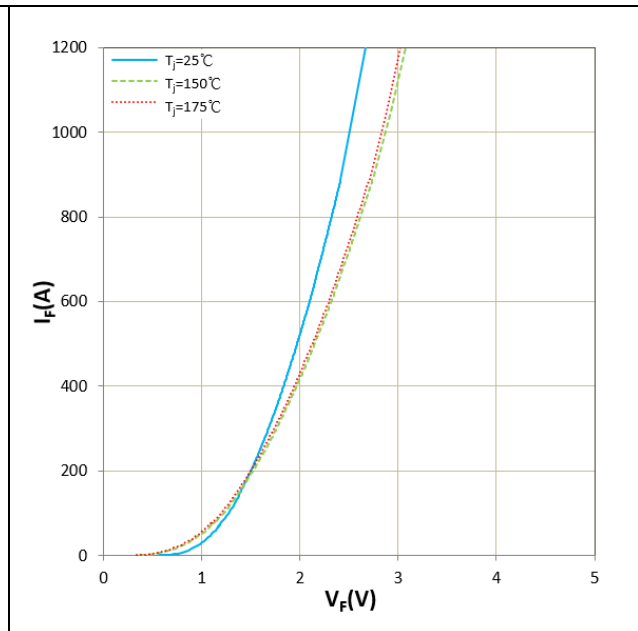


Figure 8. I_F vs V_F

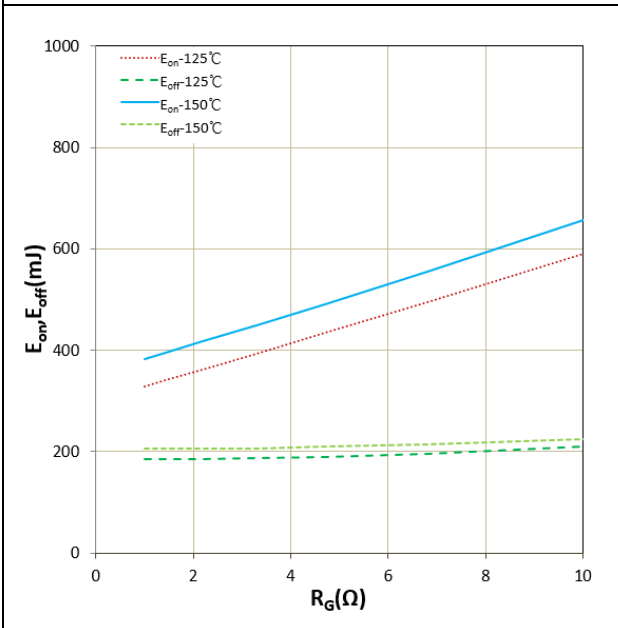


Figure 9. E_{on} , E_{off} vs R_G (Typ)
 $V_{CC} = 900V$, $V_{GE} = +15V/-8V$, $I_c = 600A$
Inductive Load

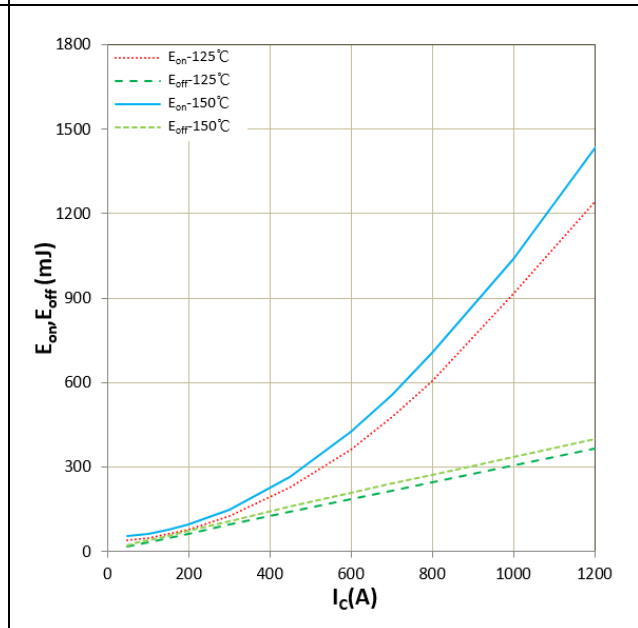


Figure 10 E_{on} , E_{off} vs I_c (Typ)
 $V_{CC} = 900V$, $V_{GE} = +15V/-8V$, $R_G = 1.0\Omega$
Inductive Load

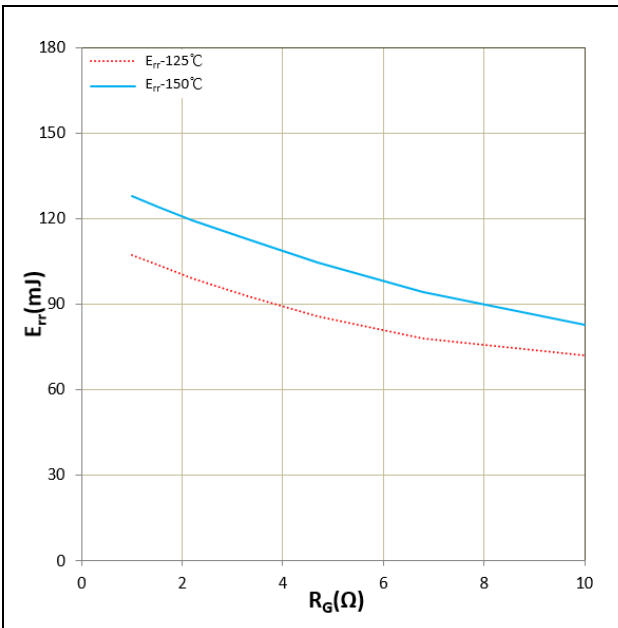


Figure 11. E_{rr} vs R_G (Typ)
 $V_{CC}=900V$, $V_{GE}=+15V/-8V$, $I_F=600A$
 Inductive Load

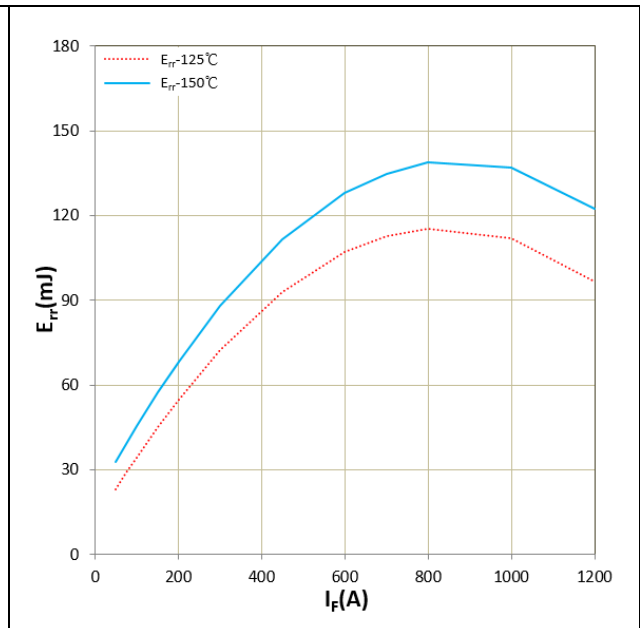


Figure 12. E_{rr} vs I_F (Typ)
 $V_{CC}=900V$, $V_{GE}=+15V/-8V$, $R_G=1.0\Omega$
 Inductive Load

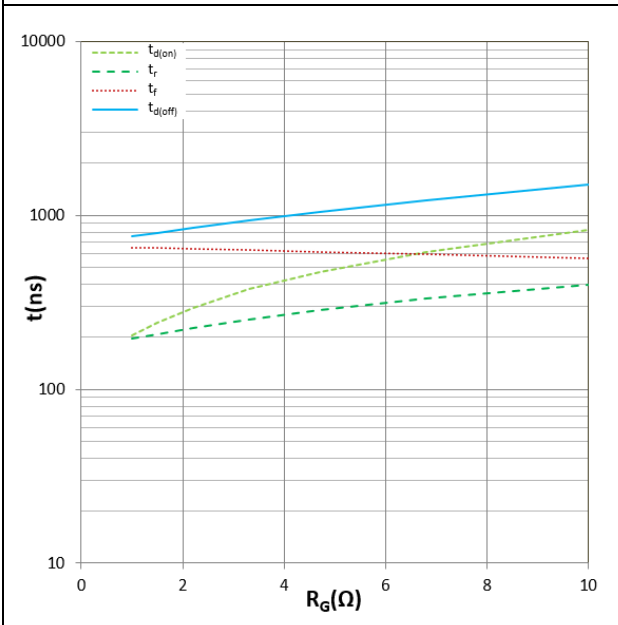


Figure 13. Switching time vs R_G (Typ)
 $V_{CC}=900V$, $V_{GE}=+15V/-8V$, $I_C=600A$
 $T_j=150^\circ C$, Inductive Load

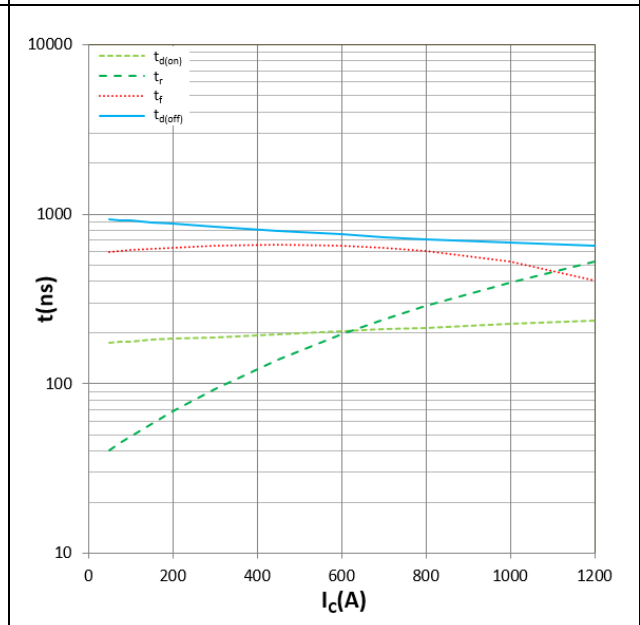


Figure 14. Switching time vs I_C (Typ)
 $V_{CC}=900V$, $V_{GE}=+15V/-8V$, $R_G=1.0\Omega$
 $T_j=150^\circ C$, Inductive Load

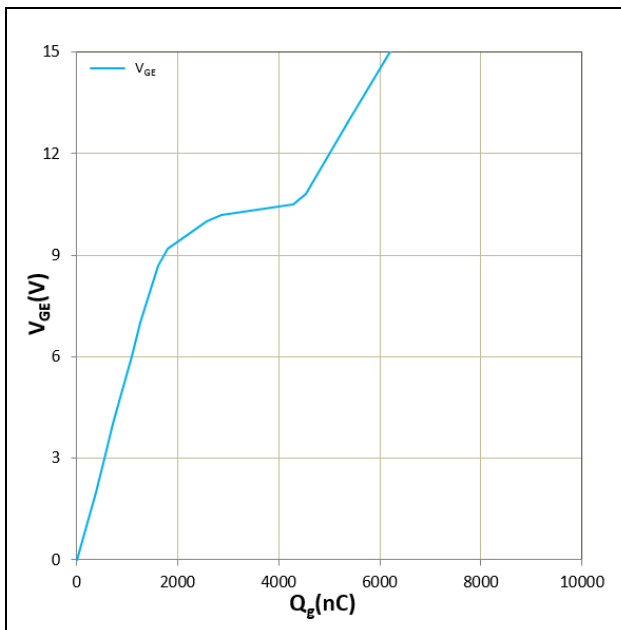


Figure 15. Gate charge

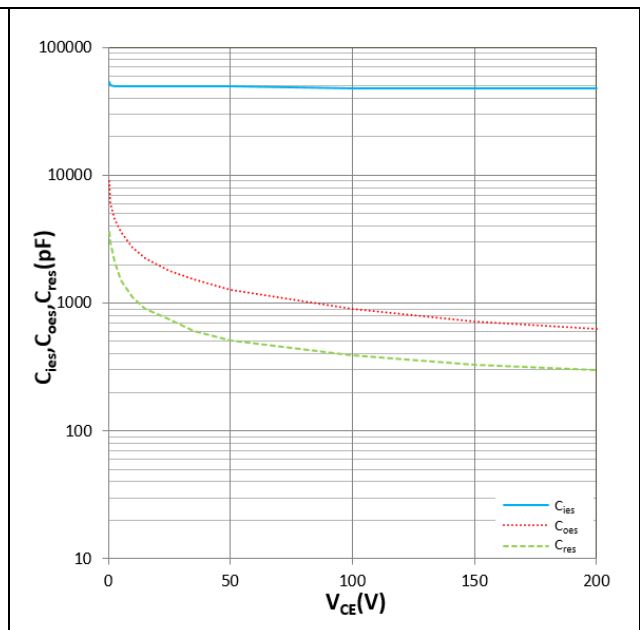


Figure 16. C_{ies}, C_{oes}, C_{res} vs V_{CE}
T_j=25°C, f=1MHz

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